

Silicon NPN Power Transistors

3DD15D

DESCRIPTION

- With TO-3 package
- High breakdown voltage
- Low collector saturation voltage

APPLICATIONS

- For B/W TV horizontal output and power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

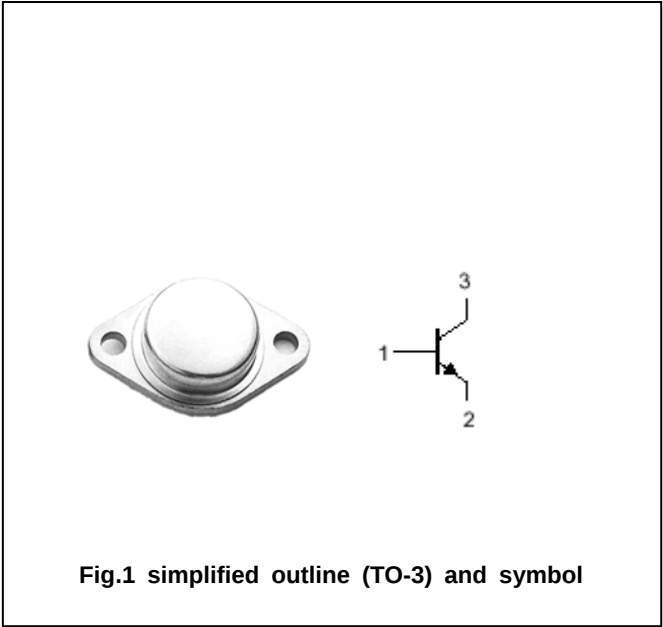


Fig.1 simplified outline (TO-3) and symbol

Absolut maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		5	A
P _C	Collector power dissipation	T _C =75℃	50	W
T _j	Junction temperature		-55~175	℃
T _{stg}	Storage temperature		-55~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	2.0	℃/W

Silicon NPN Power Transistors**3DD15D****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A ; I _B =0.25A			1.5	V
I _{CEO}	Collector cut-off current	V _{CE} =50V ; I _B =0			1.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =150V ; I _E =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			0.5	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =10V	30		250	

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PACKAGE OUTLINE

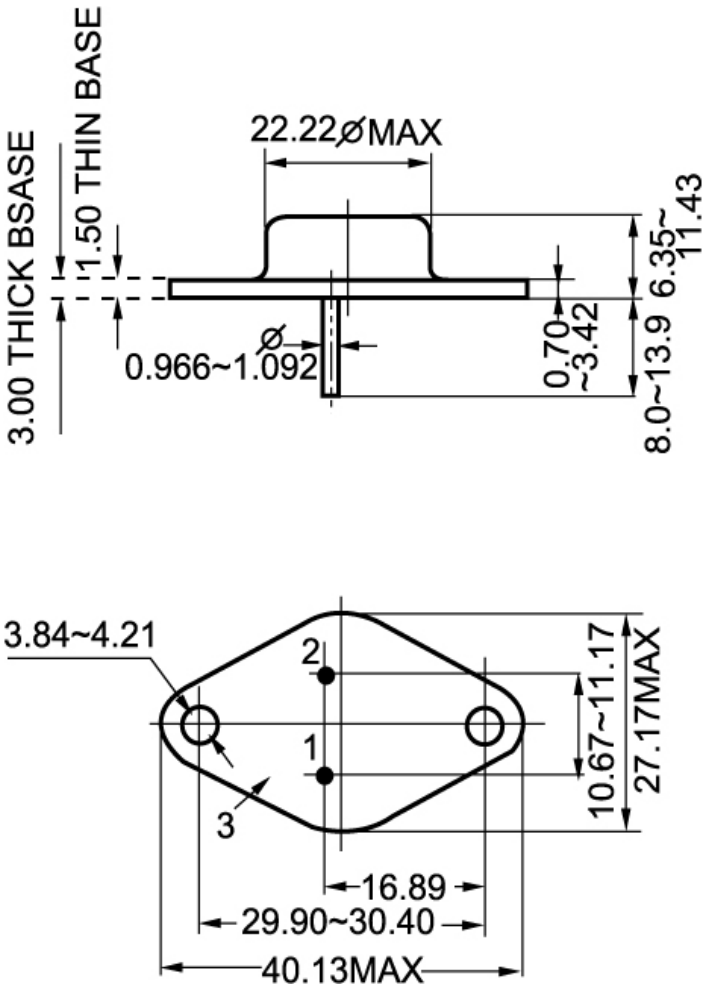


Fig.2 Outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)